STATEMENT UNDER 37 CFR 3.73(b)

Applicant/Patent Owner: _Samsung Electronics Co., Ltd._

Application No./Patent No.: _10/700,592_ Filed/Issue Date: _November 5, 2003_

Entitled: Non-Volatile Memory And Method Of Erasing For Nonvolatile Memory

Samsung Electronics Co., Ltd. , a _Corporation_
(Name of Assignee) (Type of Assignee, e.g., corporation, partnership, university, government agency, etc.)

states that it is:
1. [✓] the assignee of the entire right, title, and interest; or

2. [ ] an assignee of less than the entire right, title and interest
(The extent (by percentage) of its ownership interest is_____ %)

in the patent application/patent identified above by virtue of either:

A.[ ] An assignment from the inventor(s) of the patent application/patent identified above. The assignment was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.

OR

B.[✓] A chain of title from the inventor(s), of the patent application/patent identified above, to the current assignee as follows:
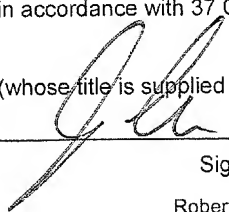
1. From: _____Inventors_____ To: _Renesas Technology Corp._____
The document was recorded in the United States Patent and Trademark Office at
Reel _014682____, Frame _0411_____, or for which a copy thereof is attached.

2. From: _____Renesas Technology Corp._____ To: _Samsung Electronics Co., Ltd._____
The document was recorded in the United States Patent and Trademark Office at
Reel _021172_____, Frame _0367_____, or for which a copy thereof is attached.

3. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at
Reel _____, Frame _____, or for which a copy thereof is attached.

[ ] Additional documents in the chain of title are listed on a supplemental sheet.

[ ] As required by 37 CFR 3.73(b)(1)(i), the documentary evidence of the chain of title from the original owner to the assignee was, or concurrently is being, submitted for recordation pursuant to 37 CFR 3.11.

[NOTE: A separate copy (*i.e.*, a true copy of the original assignment document(s)) must be submitted to Assignment Division in accordance with 37 CFR Part 3, to record the assignment in the records of the USPTO. See MPEP 302.08]

The undersigned (whose title is supplied below) is authorized to act on behalf of the assignee.

Signature	August 29, 2008
	Date
Robert N. Crouse	919-854-1400
Printed or Typed Name	Telephone Number
Myers Bigel Sibley & Sajovec, P.A.	
Title	

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REVOCATION OF POWER OF ATTORNEY, NEW POWER OF ATTORNEY BY ASSIGNEE AND CHANGE OF CORRESPONDENCE ADDRESS

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

Customer No. 20792
Myers Bigel Sibley & Sajovec, P.A.
P. O. Box 37428
Raleigh, North Carolina 27627
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Facsimile: (919) 854-1401

Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patents or patent applications identified to Renesas Technology Corp. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: _____

Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: July 7, 2008

Application No.	Patent No.	Filing Date	Assignment Recorded	Reel	Frame	Title of Patent
08/841612	5,870,218	04/30/1997	Hitachi Ltd.	008541	0020	Non-volatile Semiconductor Memory Device Which Stores Multi-Value Information
			Renesas	019287	0688	
			Samsung	021172	0367	
09/096457	5,982,667	06/11/1998	Renesas	019287	0746	Non-volatile Semiconductor Memory Device For Storing Multivalue Information By Controlling Erase And Plural Write States of Each Memory Cell
			Samsung	021172	0367	
09/339960	6,181,603	06/25/1999	Renesas	019287	0750	Non-volatile Semiconductor Memory Device Having Plural Memory Cells Which Store Multi-Value Information
			Samsung	021172	0367	
09/715106	6,396,736	11/20/2000	Renesas	019287	0754	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
10/154853	6,771,537	05/28/2002	Renesas	014569	0585	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
10/832311	7,031,187	April 27, 2004	Renesas	021134	0753	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
11/332206	7,245,532	January 17, 2006	Samsung	021172	0367	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/595880	7,394,697	November 13, 2006	Samsung	021172	0367	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information

						Information
12/117918		May 9, 2008	Renesas / Samsung	021134	0584	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
07/704739	5,300,802	May 20, 1991	Renesas / Samsung	021076 / 021172	0845 / 0367	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/179960	5,407,853	January 11, 1994	Renesas / Samsung	021076 / 021172	0845 / 0367	Method of Making Semiconductor Integrated Circuit Device Having Single-Element Type Non-Volatile Memory Elements
08/422941	5,656,839	April 17, 1995	Renesas / Samsung	021076 / 021172	0845 / 0367	Semiconductor Integrated Circuit Device Having Single-Element Type Nonvolatile Memory Elements
08/422940	5,629,541	April 17, 1995	Renesas / Samsung	021076 / 021172	0845 / 0367	Semiconductor Memory Device Constituted by Single Transistor Type Non-volatile Cells and Facilitated for Both Electrical Erasing and Writing of Data
08/451268	5,656,522	May 30, 1995	Renesas / Samsung	021076 / 021172	0845 / 0367	Method of Manufacturing a Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/885184	5,904,518	June 30, 1997	Renesas / Samsung	021076 / 021172	0845 / 0367	Method of Manufacturing a Semiconductor IC Device Having Single Transistor Type Nonvolatile Memory Cells
09/282204	6,255,690	March 31, 1999	Renesas / Samsung	021076 / 021172	0845 / 0367	Non-volatile Semiconductor Memory Device

APPENDIX A

Application No.	Patent No.	Issue Date	Party			Title
09/873451	6,451,643	June 5, 2001	Samsung	021172	0367	Method of Manufacturing a Semiconductor Device Having Non-volatile Memory Cell Portion with Single Transistor Type Memory Cells and Peripheral Portion with MISFETs
			Renesas	021076	0845	
10/164626	6,777,282	June 10, 2002	Samsung	021172	0367	Method of Manufacturing a Semiconductor Memory Device Having a Memory Cell Portion Including MISFETs With a Floating Gate and a Peripheral Circuit Portion With MISFETs
			Renesas	014569	0585	
10/819205	6,960501	April 7, 2004	Samsung	021172	0367	Method of Manufacturing a Semiconductor Memory Device Having a Non-volatile Memory Cell Portion with Single MISFET Transistor Type Memory Cells and a Peripheral Circuit Portion with MISFETs
			Renesas	021076	0845	
11/393774	7,399,667	March 31, 2006	Samsung	021172	0367	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
			Renesas	021076	0845	
11/220723	7,071,050	September 8, 2005	Samsung	021172	0367	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
			Renesas	021076	0845	
08/913338	5,978,941	September 11, 1997	Samsung	021172	0367	Semiconductor Memory Device Having Deterioration Determining Function
			Hitachi, Ltd.	008892	0596	
			Renesas	021076	0845	
09/432389	6,223,311	November 2, 1999	Samsung	021172	0367	Semiconductor Memory Device Having Deterioration Determining Function
			Renesas	021076	0845	

Application No.	Patent No.	Date	Party			Title
09/794073	6,694,460	February 28, 2001	Renesas Samsung	014569 021172	0585 0367	Semiconductor Memory Device Having Deterioration Determining Function
07/517386	5,079,603	April 30, 1990	Renesas Samsung	021076 021172	0845 0367	Semiconductor Memory Device
07/765065	5,189,497	September 24, 1991	Renesas Samsung	021076 021172	0845 0367	Semiconductor Memory Device
07/992473	5,340,760	December 15, 1992	Renesas Samsung	021076 021172	0845 0367	Method of Manufacturing EEPROM Memory Device
08/260229	5,472,891	June 14, 1994	Renesas Samsung	021076 021172	0845 0367	Method of Manufacturing a Semiconductor Device
08/419232	5,604,142	April 10, 1995	Renesas Samsung	021076 021172	0845 0367	Method of Making an EPROM With Peripheral Transistor
11/082992	7,242,611	March 18, 2005	Renesas Samsung	016400 021172	0869 0367	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
11/819015		June 25, 2007	Renesas Samsung	016400 021172	0869 0367	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
11/819016		June 25, 2007	Renesas Samsung	016400 021172	0869 0367	Non-volatile Semiconductor Memory Device for Writing Multivalued Data
09/620719	6,496,409	July 20, 2000	Mitsubishi	010954	0262	Variable Capacity Semiconductor Memory

			Device			
			Renesas	021118	0337	
			Samsung	021172	0367	
08/203303	5,422,856	March 1, 1994	Hitachi	007374	0104	Non-volatile Memory Programming at Arbitrary Timing Based on Current Requirements
			Renesas	021029	0409	
			Samsung	021172	0367	
10/700592	7,068,541	November 5, 2003	Renesas	014682	0411	Nonvolatile Memory and Method of Erasing for Nonvolatile Memory
			Samsung	021172	0367	
11/284949	7,072,224	November 23, 2005	Samsung	021172	0367	Nonvolatile Memory and Method of Erasing for Nonvolatile Memory